



## **RF3800**

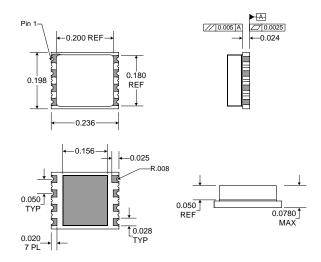
#### GaAs HBT PRE-DRIVER AMPLIFIER

## **Typical Applications**

- Pre-Driver for 450 MHz Basestation Amplifiers
- PA Stage for Commercial Wireless Infrastructure
- Class AB Operation for Cellular Radio and Wireless Local Loop

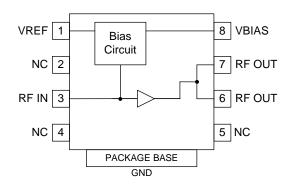
## **Product Description**

The RF3800 is specifically designed for wireless infrastructure applications in 450MHz. Using a highly reliable GaAs HBT fabrication process, this high-performance single-stage amplifier achieves high output power over a broad frequency range. The RF3800 also provides excellent efficiency and thermal stability through the use of a thermally-enhanced surface-mount AIN package. Ease of integration is accomplished through the incorporation of an optimized evaluation board design provided to achieve proper 50 $\Omega$  operation. Various evaluation board bias configurations are available to address a broad range of wireless infrastructure applications.



#### **Optimum Technology Matching® Applied**

🗌 Si BJT	GaAs HBT	GaAs MESFET
🗌 Si Bi-CMOS	SiGe HBT	Si CMOS
InGaP/HBT	GaN HEMT	SiGe Bi-CMOS



#### **Functional Block Diagram**

#### Package Style: AIN

#### **Features**

- 6W Output Power
- High Linearity
- 45% Power-Added Efficiency
- Thermally-Enhanced Packaging
- Broadband Platform Design Approach

#### **Ordering Information**

RF3800 GaAs HBT Pre-Driver Amplifier RF3800PCBA-416 Fully Assembled Evaluation Board

 RF Micro Devices, Inc.
 Tel (336) 664 1233

 7628 Thorndike Road
 Fax (336) 664 0454

 Greensboro, NC 27409, USA
 http://www.rfmd.com

# **RF3800**

Please contact RF Micro Devices Applications Engineering at (336) 678-5570 for more information.